IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants:	Eliyahou Harari et al.		
Title:	Non-Volatile memory Cells Utilizing Substrate Trenches		
Application No.:	09/925,134	Filing Date:	August 8, 2001
Examiner:	Quinto, Kevin V.	Group Art Unit:	2826
Docket No.:	SNDK.111US1	Conf. No.:	6957

Certificate of Mailing Under 37 CFR 1.8

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on January 8, 2004

Mary E. Buggie
Signature

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Dear Sir:

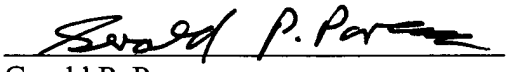
Pursuant to 37 C.F.R. §§ 1.56, 1.97 and 1.98, Applicants call the documents listed on the enclosed Form PTO-1449 to the Examiner's attention in this patent application. Copies of the documents listed on the accompanying Form PTO-1449 are enclosed.

Citation of these documents shall not be construed as (1) an admission that the documents are prior art with respect to the invention or inventions claimed in this application, (2) a representation that a search has been made (other than as indicated by any cited document), or (3) an admission that the cited information is, or is considered to be, material to patentability as defined in § 1.56(b).

This information disclosure statement is submitted under 37 C.F.R. § 1.97(c). A check including $180.00 for the information disclosure statement fee under 37 C.F.R. § 1.17(p), is

enclosed. The Commissioner is authorized, however, to charge any fee that may be required, or to credit any overpayment, against Deposit Account No. 502664, as set forth in the accompanying transmittal letter.

Respectfully submitted,



January 8, 2004
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U.S. Department of Commerce, Patent and Trademark	Atty. Docket No.	Application No.
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(Use several sheets if necessary)	Harari et al.	6957
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U.S. Patent Documents

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	1	4,112,507	9/5/78	White et al.			
	2	5,070,032	12/3/91	Yuan et al.			
	3	5,095,344	3/10/92	Harari			
	4	5,168,344	12/1/92	Mitchell et al.			
	5	5,172,338	12/15/92	Mehrotra et al.			
	6	5,313,421	5/17/94	Guterman et al.			
	7	5,315,541	5/24/94	Harari et al.			
	8	5,343,063	8/30/94	Yuan et al.			
	9	5,579,259	11/26/96	Samachisa et al.			
	10	5,661,053	8/26/97	Yuan			

U.S. Published Patent Application Documents

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	11	2002/0130350	9/19/02	Shin et al.			

Foreign Patent Documents

							Translation	
		Document	Date	Country	Class	Subclass	Yes	No

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	12	Chan et al., "A True Single-Transistor Oxide-Nitride-Oxide EEPROM Device," *IEEE Electron Device Letters*, Vol. EDL-8, No. 3, March 1987, pp. 93-95.
	13	Nozaki et al., "A 1-Mb EEPROM with MONOS Memory Cell for Semiconductor Disk Application," *IEEE Journal of Solid State Circuits*, Vol. 26, No. 4, April 1991, pp. 497-501.
	14	Eitan et al., "NROM: A Novel Localized Trapping, 2-Bit Nonvolatile Memory Cell," *IEEE Electron Device Letters*, Vol. 21, No. 11, November 2000, pp. 543-545.

Examiner	Date Considered

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.

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U.S. Patent Documents

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	15	5,712,180	1/27/98	Guterman et al.			
	16	5,851,881	12/22/98	Lin et al.			
	17	6,011,725	6/4/00	Eitan			
	18	6,103,573	8/15/00	Harari et al.			
	19	6,137,718	10/24/00	Reisinger			
	20	6,151,248	11/21/00	Harari et al.			
	21	6,222,762	4/24/01	Guterman et al.			
	22	6,248,633	6/19/01	Ogura et al.			
	23	6,281,075	8/28/01	Yuan et al.			
	24	6,512,263	1/28/03	Yuan et al.			
	25	6,532,172	3/11/03	Harari et al.			

U.S. Published Patent Application Documents

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	26	2002/0118574	8/29/02	Gongwer et al.			

Foreign Patent Documents

							Translation	
		Document	Date	Country	Class	Subclass	Yes	No

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	27	DiMaria et al., "Electrically-Alterable Read-Only-Memory Using Si-rich $SI0_2$ Injectors and a Floating Polycrystalline Silicon Storage Layer," *J. Appl. Phys.* 52(7), July 1981, pp. 4825-4842.
	28	Hori et al., "A MOSFET with Si-Implanted Gate-$Si0_2$ Insulator for NonVolatile Memory Applications," IEDM 92, April 1992, pp. 469-472.

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